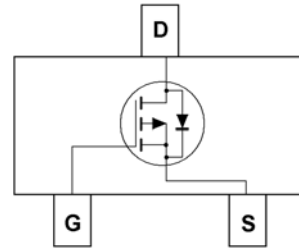


P-Channel Enhancement Mode MOSFET

Feature

- -16V/-3A, $R_{DS(ON)} = 160m\Omega (MAX) @V_{GS} = -4.5V$.
 $R_{DS(ON)} = 240m\Omega (MAX) @V_{GS} = -2.5V$.
- Super High dense cell design for extremely low $R_{DS(ON)}$
- Reliable and Rugged
- SC-59 for Surface Mount Package



Applications

- Power Management
Portable Equipment and Battery Powered Systems.

Absolute Maximum Ratings $T_A=25^{\circ}C$ Unless Otherwise noted

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V_{DS}	-16	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current-Continuous	I_D	-3	A

Electrical Characteristics $T_A=25^{\circ}C$ Unless Otherwise noted

Parameter	Symbol	Test Conditions	Min	Typ.	Max	Units
Off Characteristics						
Drain to Source Breakdown Voltage	BVDSS	$V_{GS}=0V, I_D=-250\mu A$	-16	-	-	V
Zero-Gate Voltage Drain Current	IDSS	$V_{DS}=-12V, V_{GS}=0V$	-	-	-5	μA
Gate Body Leakage Current, Forward	IGSSF	$V_{GS}=8V, V_{DS}=0V$	-	-	100	nA
Gate Body Leakage Current, Reverse	IGSSR	$V_{GS}=-8V, V_{DS}=0V$	-	-	-100	nA
On Characteristics						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_D=-250\mu A$	-0.45	-	-1.5	V
Static Drain-source	RDS(ON)	$V_{GS}=-4.5V, I_D=-3.0A$	-	120	160	$m\Omega$
On-Resistance		$V_{GS}=-2.5V, I_D=-2.0A$	-	160	240	$m\Omega$
Drain-Source Diode Characteristics and Maximum Ratings						
Drain-Source Diode Forward Voltage	VSD	$V_{GS}=0V, I_S=-1.25A$			-1.8	V

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Typical Characteristics

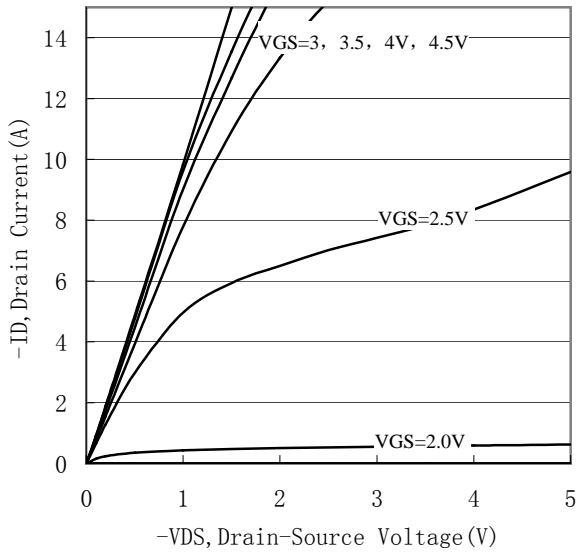


Figure 1. Output Characteristics

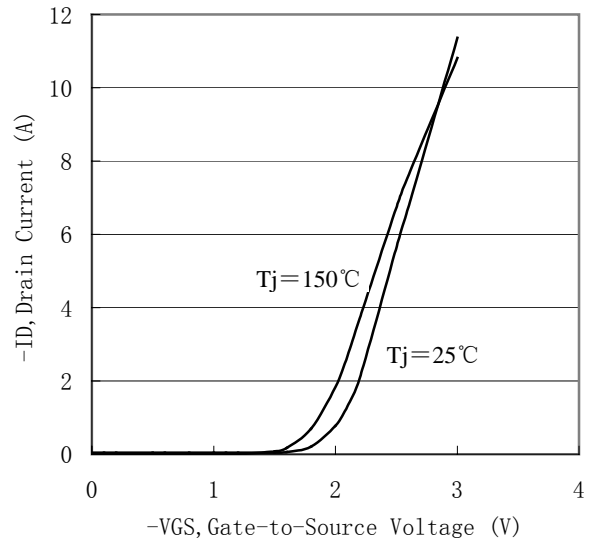


Figure 2. Transfer Characteristics

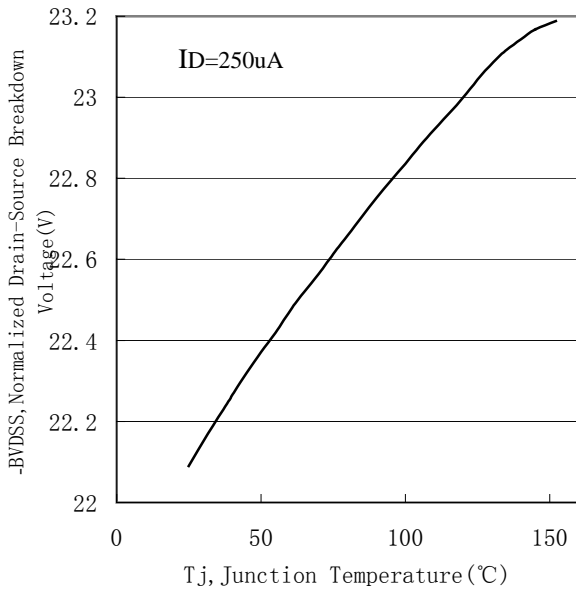


Figure 3. Breakdown Voltage Variation with Temperature

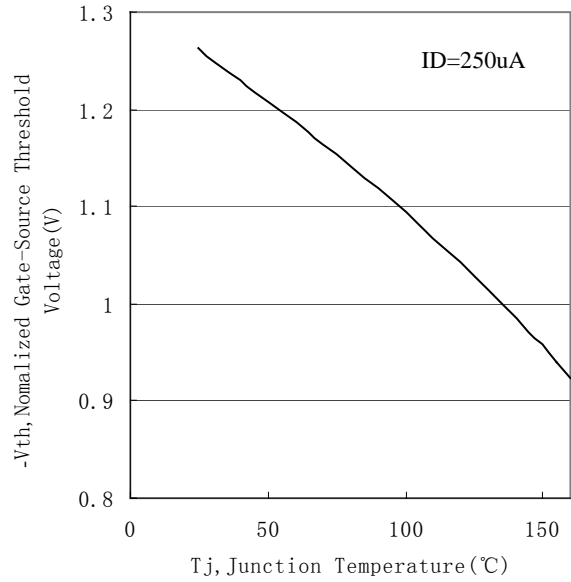


Figure 4. Gate Threshold Variation with Temperature

Typical Characteristics

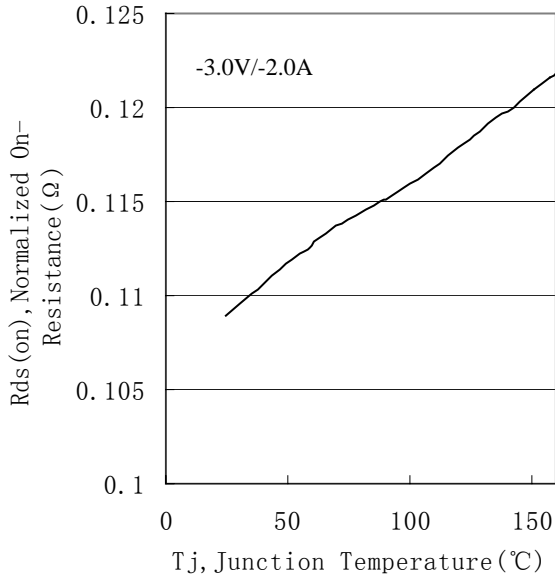


Figure 5. On-Resistance Variation with Temperature

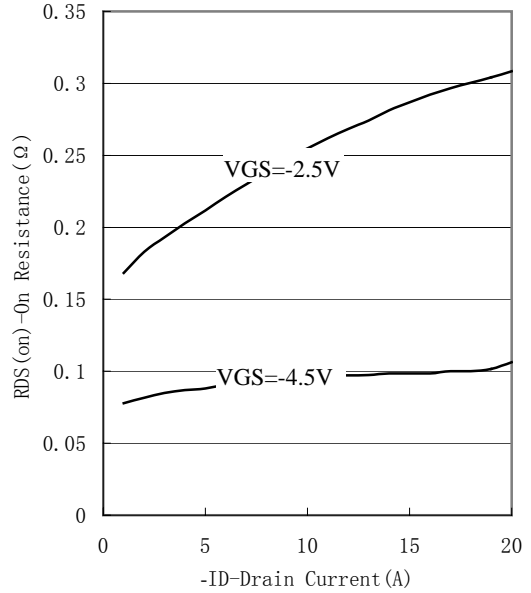


Figure 6. On-Resistance vs. Drain Current

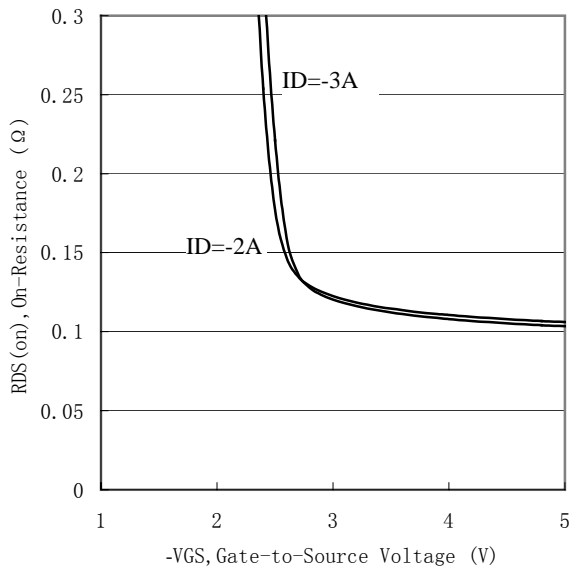


Figure 7. On-Resistance vs. Gate-to-Source Voltage

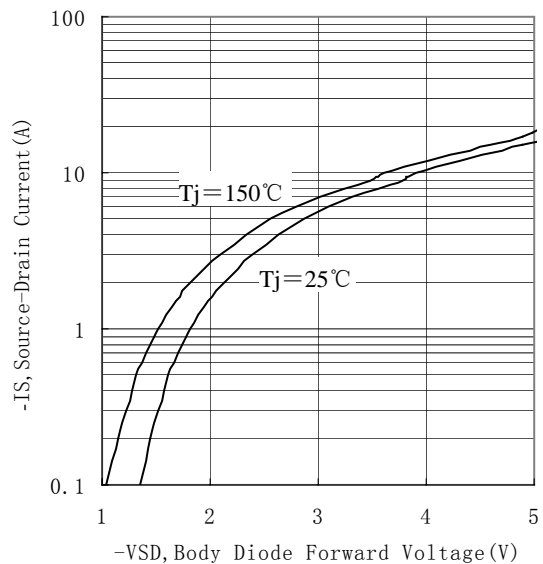


Figure 8. Source-Drain Diode Forward Voltage